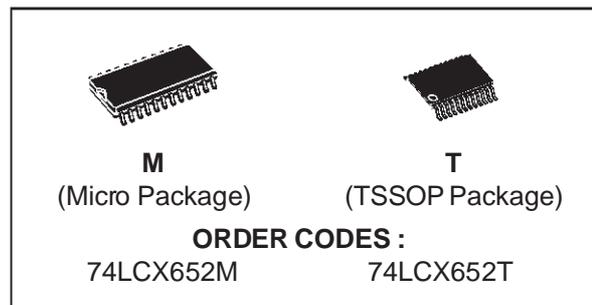




74LCX652

LOW VOLTAGE CMOS OCTAL BUS TRANSCEIVER/REGISTER (3-STATE) WITH 5V TOLERANT INPUTS AND OUTPUTS

- 5V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED:
 $t_{PD} = 7.0 \text{ ns (MAX.) at } V_{CC} = 3V$
- POWER-DOWN PROTECTION ON INPUTS AND OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = |I_{OL}| = 24 \text{ mA (MIN)}$
- PCI BUS LEVELS GUARANTEED AT 24mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC} \text{ (OPR)} = 2.0V \text{ to } 3.6V \text{ (1.5V Data Retention)}$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 652
- LATCH-UP PERFORMANCE EXCEEDS 500mA
- ESD PERFORMANCE:
 $HBM > 2000V; MM > 200V$



This device consists of bus transceiver circuits with 3-state outputs, D type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal storage registers. Enable (GAB) and (GBA) pins are provided to control the transceiver functions.

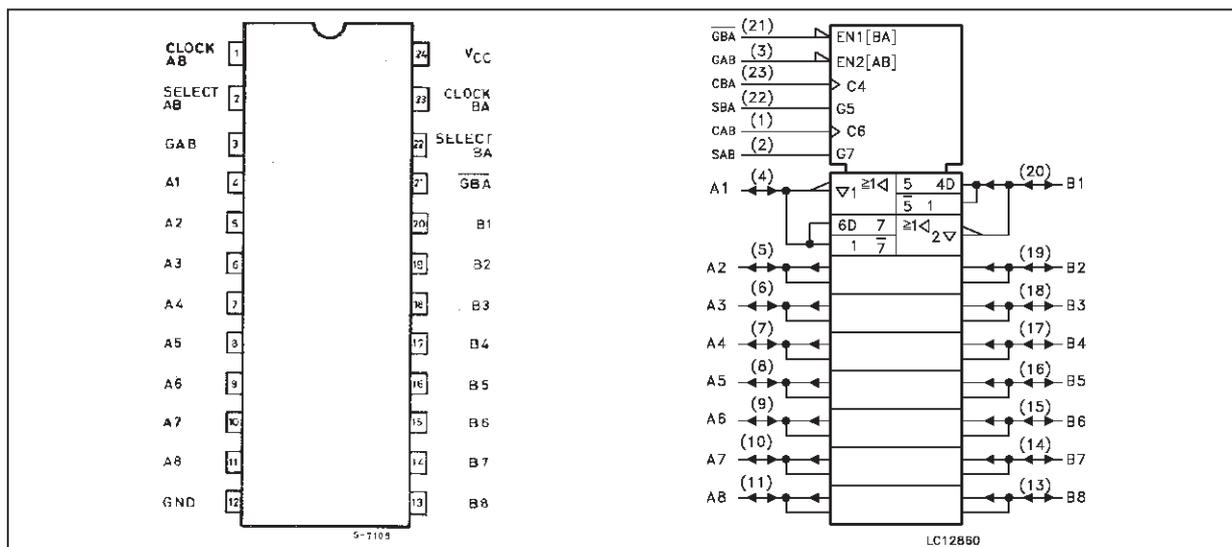
Select AB and Select BA control pins are provided to select whether real-time or stored data is transferred. A low input level selects real-time, and a high selects stored data.

Data on the A or B bus, or both, can be stored in the internal D flip-flop by low-to-high transitions at the appropriate clock pins (CAB or CBA) regardless of the select or enable control pins.

DESCRIPTION

The LCX652 is a low voltage CMOS OCTAL BUS TRANSCEIVER AND REGISTER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power and high speed 3.3V applications; it can be interfaced to 5V signal environment for both inputs and outputs.

PIN CONNECTION AND IEC LOGIC SYMBOLS



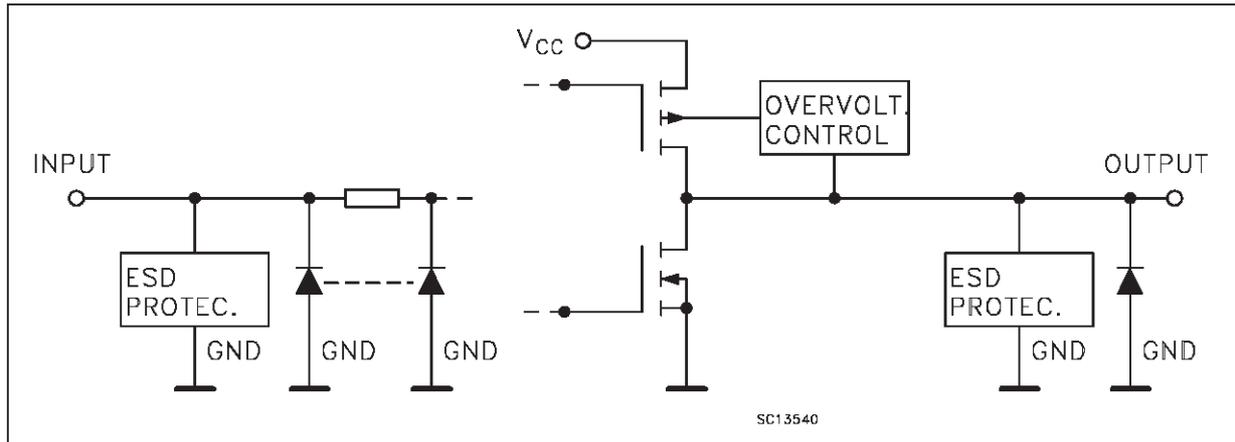
74LCX652

When select AB and select BA are in the real-time transfer mode, it is also possible to store data without using the internal D-type flip-flops by simultaneously enabling GAB or $\overline{\text{GBA}}$. In this configuration each output reinforces its input. It has same speed performance at 3.3V than 5V,

AC/ACT family, combined with a lower power consumption.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

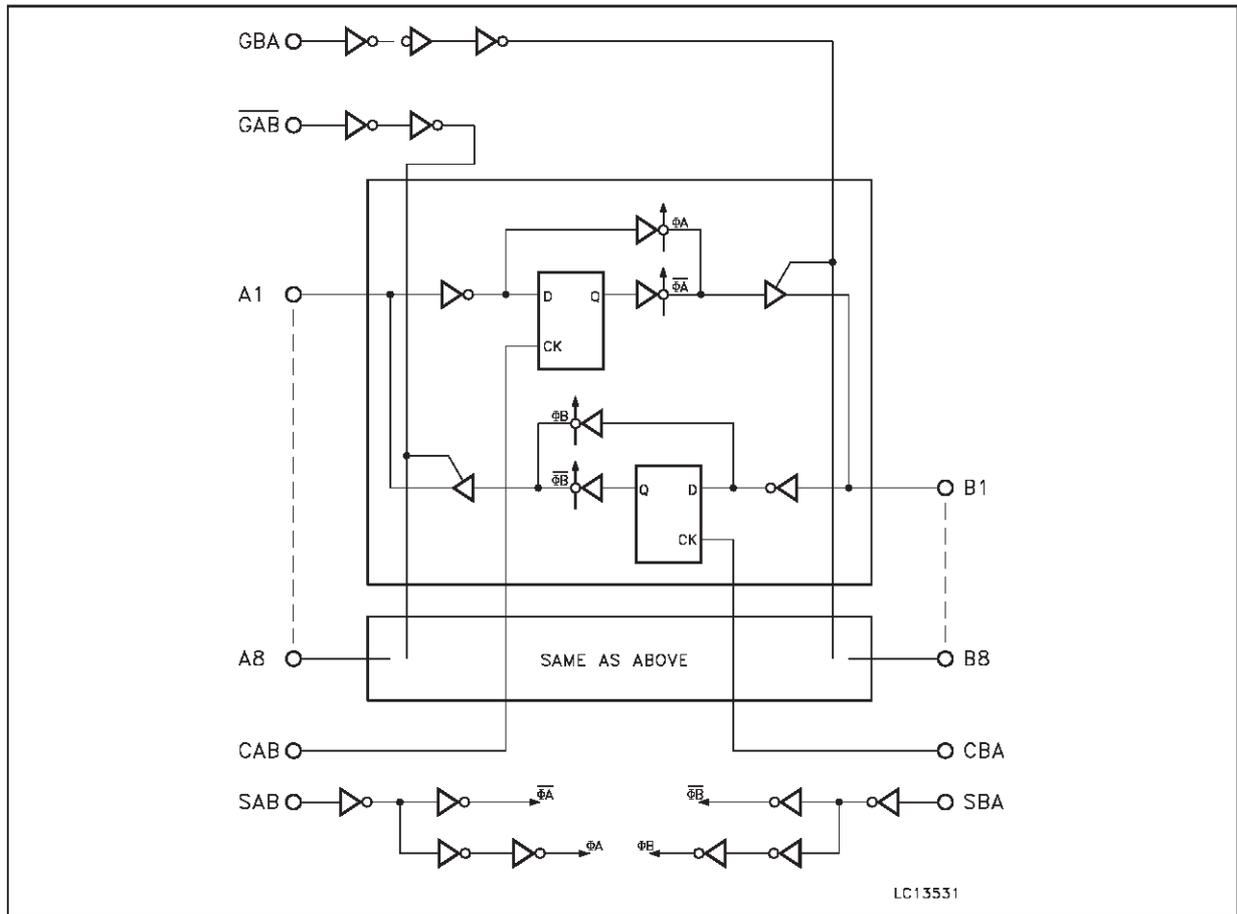
INPUT AND OUTPUT EQUIVALENT CIRCUIT



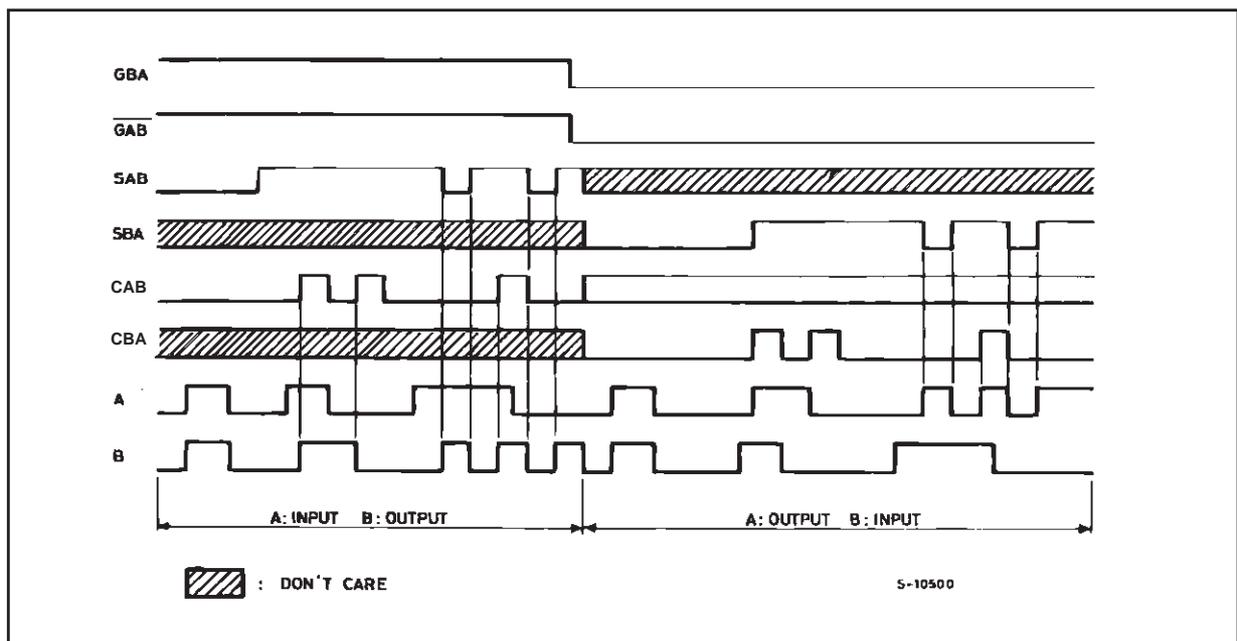
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	CAB	A to B Clock Input (LOW to HIGH, Edge-Triggered)
2	SAB	Select A to B Source Input
3	GAB	Direction Control Input
4, 5, 6, 7, 8, 9, 10, 11	A1 to A8	A Data Inputs/Outputs
20, 19, 18, 17, 16, 15, 14, 13	B1 to B8	B Data Inputs/Outputs
21	$\overline{\text{GBA}}$	Output Enable Input (Active LOW)
22	SBA	Select B to A Source Input
23	CBA	B to A Clock Input (LOW to HIGH, Edge-Triggered)
12	GND	Ground (0V)
24	Vcc	Positive Supply Voltage

LOGIC DIAGRAM



TIMING CHART



TRUTH TABLE

GAB	GBA	CAB	CBA	SAB	SBA	A	B	FUNCTION
L	H					INPUTS	INPUTS	Both the A bus and the B bus are inputs
		X	X	X	X	Z	Z	The output functions of the A and B bus are disabled
				X	X	INPUTS	INPUTS	Both the A and B busses are used as inputs to the internal flip-flops. Data on the bus will be stored on low to high transition of the clock inputs
L	L					OUTPUTS	INPUTS	The A bus are outputs and the B bus are inputs
		X*	X	X	L	L	L	The data on the B bus are displayed on the A bus
						H	H	
		X*		X	L	L	L	The data on the B bus are displayed on the A bus and are stored in the B internal flip-flop on low to high transition of the clock pulse
						H	H	
		X*	X	X	H	Qn	X	The data stored in the B internal flip-flop are displayed on the A bus
		X*		X	H	L	L	The data on the B bus are stored in the B internal flip-flop on low to high transition of the clock pulse. The states of the internal flip-flops propagate directly to the A bus
						H	H	
H	H					INPUTS	OUTPUTS	The A bus are inputs and the B bus are outputs
		X	X*	L	X	L	L	The data on the A bus are displayed on the B bus
						H	H	
			X*	L	X	L	L	The data on the A bus are displayed on the B bus and are stored in the A internal flip-flop on low to high transition of the clock pulse
						H	H	
		X	X*	H	X	X	Qn	The data stored in the A internal flip-flops are displayed on the B bus
			X*	H	X	L	L	The data on the A bus are stored in the A internal flip-flop on low to high transition of the clock pulse. The states of the internal flip-flops propagate directly on the B bus
						H	H	
H	L					OUTPUTS	OUTPUTS	Both the A bus and the B bus are outputs
		X	X	H	H	Qn	Qn	The data stored in the internal flip-flops are displayed on the A and B bus respectively

X : DON'T CARE

Z : HIGHIMPEDANCE

Qn : THE DATA STORED TO THE INTERNAL FLIP-FLOPS BY MOST RECENT LOW TO HIGH TRANSITION OF THE CLOCK INPUTS

* : THE DATA AT THE A AND B BUS WILL BE STORED TO THE INTERNAL FLIP-FLOPS ON EVERY LOW TO HIGH TRANSITION OF THE CLOCK INPUTS

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage (OFF state)	-0.5 to +7.0	V
V_O	DC Output Voltage (High or Low State) (note1)	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	- 50	mA
I_{OK}	DC Output Diode Current (note2)	± 50	mA
I_O	DC Output Source/Sink Current	± 50	mA
I_{CC}	DC Supply Current per Supply Pin	± 100	mA
I_{GND}	DC Ground Current per Supply Pin	± 100	mA
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$
T_L	Lead Temperature (10 sec)	300	$^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

1) I_O absolute maximum rating must be observed

2) $V_O < GND$, $V_O > V_{CC}$

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2.0 to 3.6	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage (OFF state)	0 to 5.5	V
V_O	Output Voltage (High or Low State)	0 to V_{CC}	V
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 3.0$ to $3.6V$)	± 24	mA
I_{OH}, I_{OL}	High or Low Level Output Current ($V_{CC} = 2.7$ to $3.0V$)	± 12	mA
T_{op}	Operating Temperature:	-40 to +85	$^{\circ}C$
dt/dv	Input Transition Rise or Fall Rate ($V_{CC} = 3.0V$) (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.5V to 3.6V

2) V_{IN} from 0.8V to 2.0V

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value		Unit
		V _{CC} (V)		-40 to 85 °C		
				Min.	Max.	
V _{IH}	High Level Input Voltage	2.7 to 3.6		2.0		V
V _{IL}	Low Level Input Voltage				0.8	V
V _{OH}	High Level Output Voltage	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O =-100 μA	V _{CC} -0.2	V
		2.7		I _O =-12 mA	2.2	
		3.0		I _O =-18 mA	2.4	
				I _O =-24 mA	2.2	
V _{OL}	Low Level Output Voltage	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O =100 μA	0.2	V
		2.7		I _O =12 mA	0.4	
		3.0		I _O =16 mA	0.4	
		3.0		I _O =24 mA	0.55	
I _I	Input Leakage Current	2.7 to 3.6	V _I = 0 to 5.5 V		±5	μA
I _{OZ}	3 State Output Leakage Current	2.7 to 3.6	V _I = V _{IH} or V _{IL} V _O = 0 to 5.5V		±5	μA
I _{off}	Power Off Leakage Current	0	V _I or V _O = 5.5V		100	μA
I _{CC}	Quiescent Supply Current	2.7 to 3.6	V _I = V _{CC} or GND		10	μA
			V _I or V _O = 3.6 to 5.5V		±10	
ΔI _{CC}	ICC incr. per input	2.7 to 3.6	V _{IH} = V _{CC} -0.6V		500	μA

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1)	3.3	C _L = 50 pF V _{IL} = 0 V V _{IH} = 3.3V		0.8		V
V _{OLV}					-0.8		

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 2.5 \text{ ns}$)

Symbol	Parameter	Test Condition		Value		Unit
		V_{CC} (V)	Waveform	-40 to 85 °C		
				Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time CAB or CBA to An or Bn	2.7 3.0 to 3.6	3	1.5 1.5	9.5 8.5	ns
t_{PLH} t_{PHL}	Propagation Delay Time An to Bn or Bn to An	2.7 3.0 to 3.6	1	1.5 1.5	8.0 7.0	ns
t_{PLH} t_{PHL}	Propagation Delay Time SAB or SBA to An or Bn	2.7 3.0 to 3.6	1	1.5 1.5	9.5 8.5	ns
t_{PZL} t_{PZH}	Output Enable Time GAB, GBA to An or Bn	2.7 3.0 to 3.6	2	1.5 1.5	9.5 8.5	ns
t_{PLZ} t_{PHZ}	Output Disable Time GAB, GBA to An or Bn	2.7 3.0 to 3.6	2	1.5 1.5	9.5 8.5	ns
t_s	Setup Time, HIGH or LOW Level Data to CAB, CBA	2.7 3.0 to 3.6	3	2.5 2.5		ns
t_h	Hold Time, HIGH or LOW Level Data to CAB, CBA	2.7 3.0 to 3.6	3	1.5 1.5		ns
t_w	CAB, CBA Pulse Width, HIGH or LOW	2.7 3.0 to 3.6	4	4.0 3.3		ns
f_{MAX}	Clock Pulse Frequency	3.0 to 3.6	3	150		MHz
t_{OSLH} t_{OSHL}	Output to Output Skew Time (note 1, 2)	3.0 to 3.6			1.0	ns

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHl}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLl}|$)

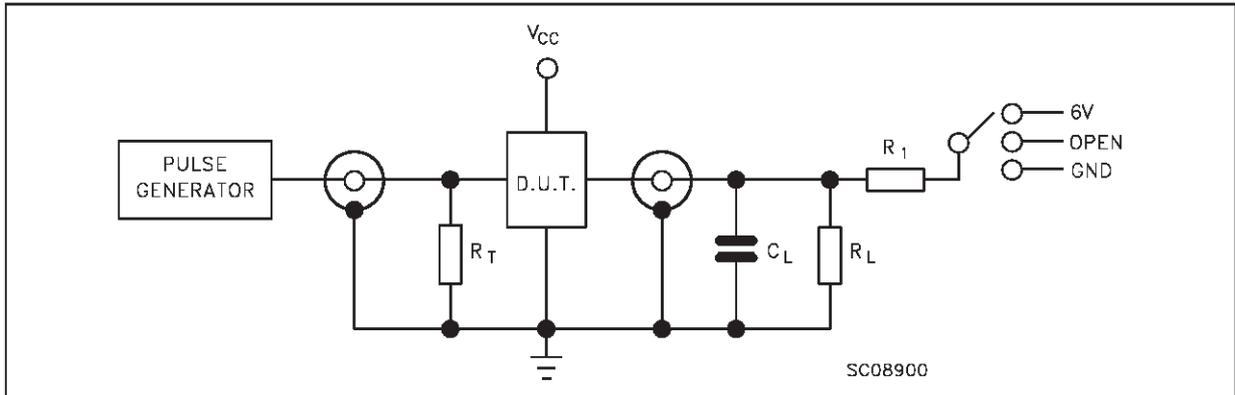
2) Parameter guaranteed by design

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
		V_{CC} (V)		$T_A = 25 \text{ °C}$			
				Min.	Typ.	Max.	
C_{IN}	Input Capacitance	3.3	$V_{IN} = 0 \text{ to } V_{CC}$		6		pF
$C_{i/o}$	I/O Capacitance	3.3	$V_{IN} = 0 \text{ to } V_{CC}$		10		pF
C_{PD}	Power Dissipation Capacitance (note 1)	3.3	$f_{IN} = 10\text{MHz}$ $V_{IN} = 0 \text{ or } V_{CC}$		36		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per circuit)

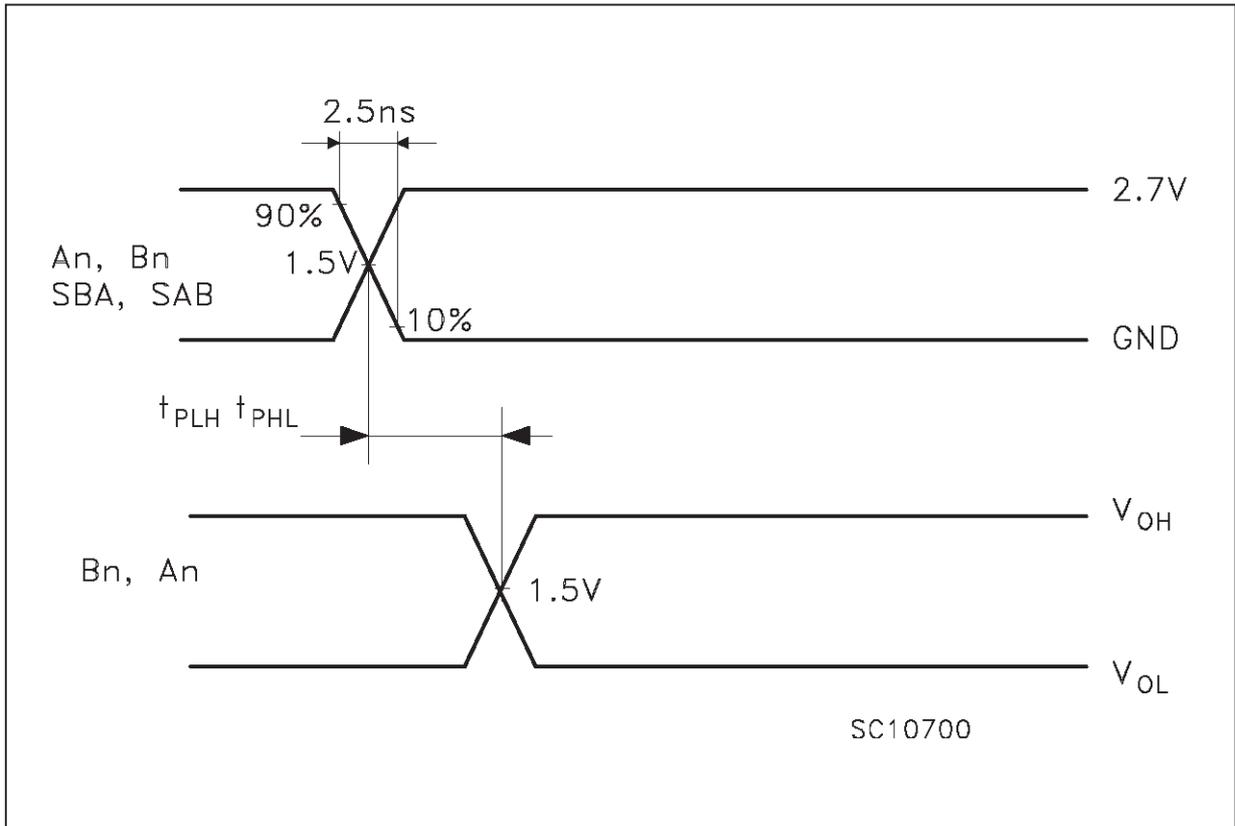
TEST CIRCUIT

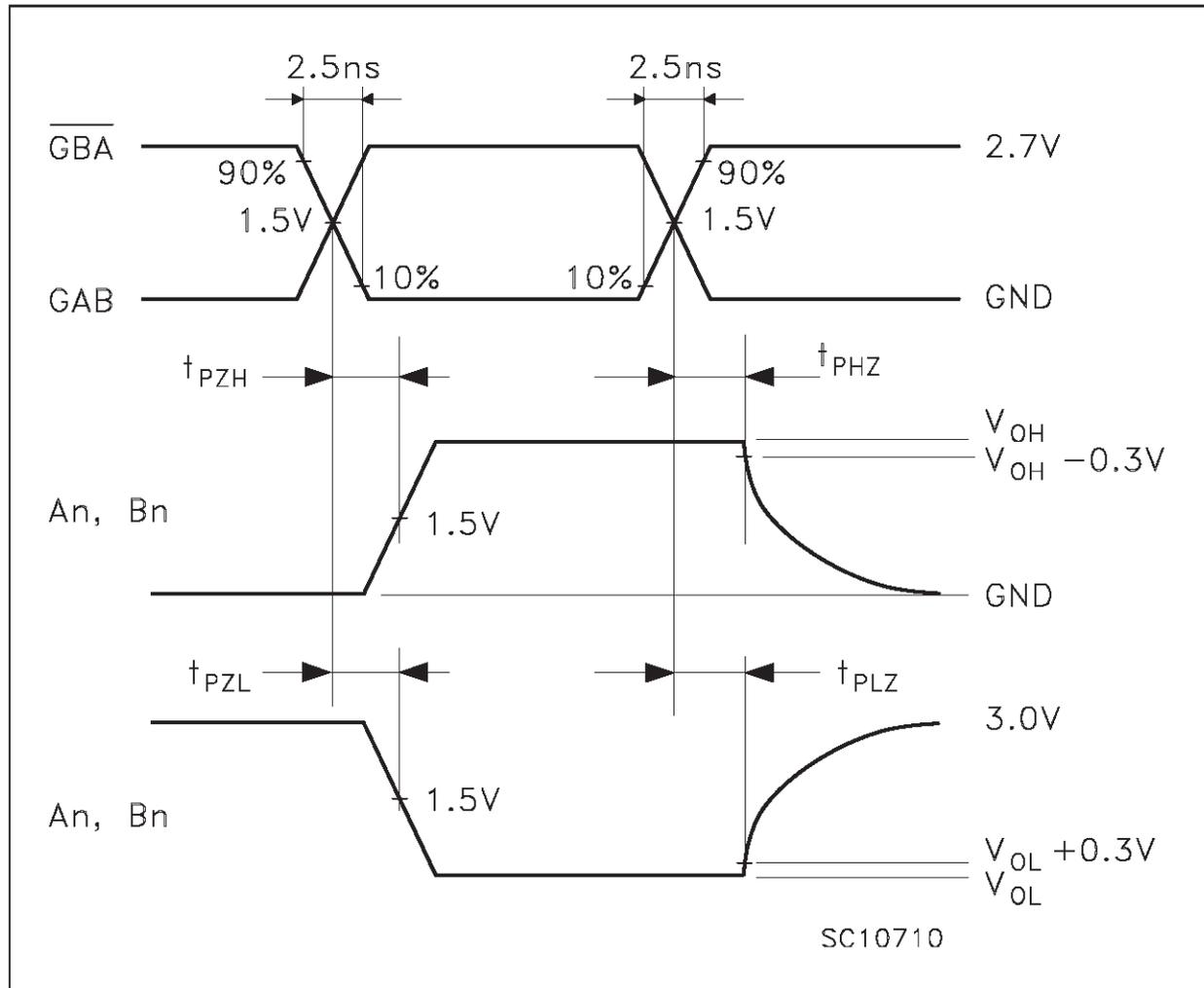


TEST	SWITCH
t_{PLH} , t_{PHL}	Open
t_{PZL} , t_{PLZ}	6V
t_{PZH} , t_{PHZ}	GND

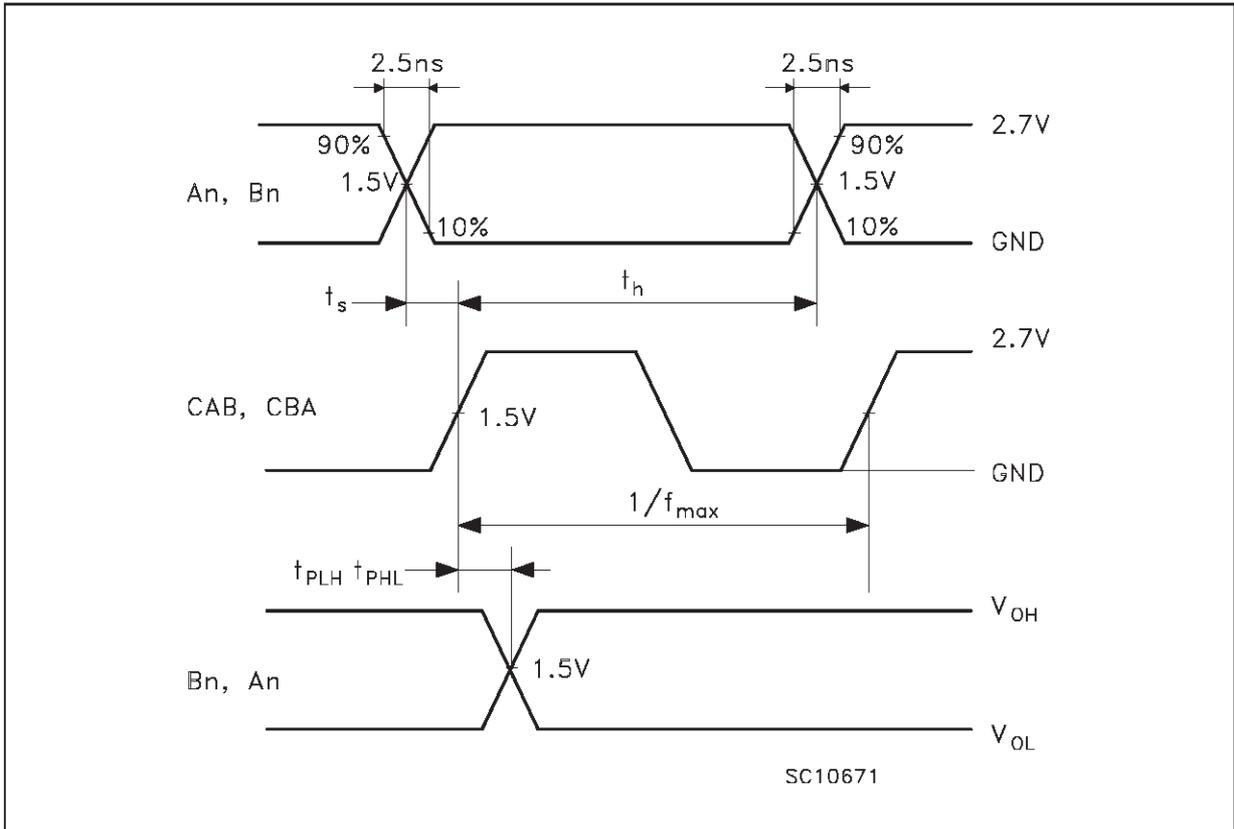
C_L = 50 pF or equivalent (includes jig and probe capacitance)
 $R_L = R_1 = 500\Omega$ or equivalent
 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

WAVEFORM 1: PROPAGATION DELAYS, SAB, SBA, An, Bn TIMES (f=1MHz; 50% duty cycle)

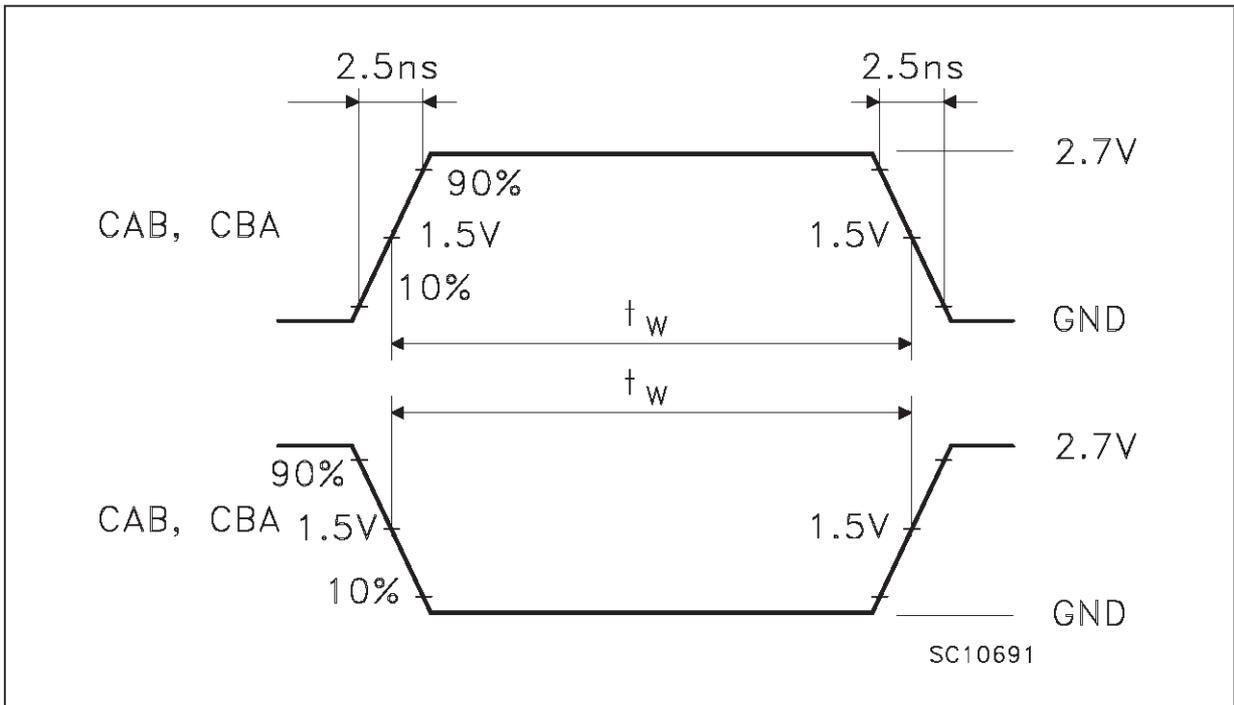


WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIMES ($f=1\text{MHz}$; 50% duty cycle)


WAVEFORM 3: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)

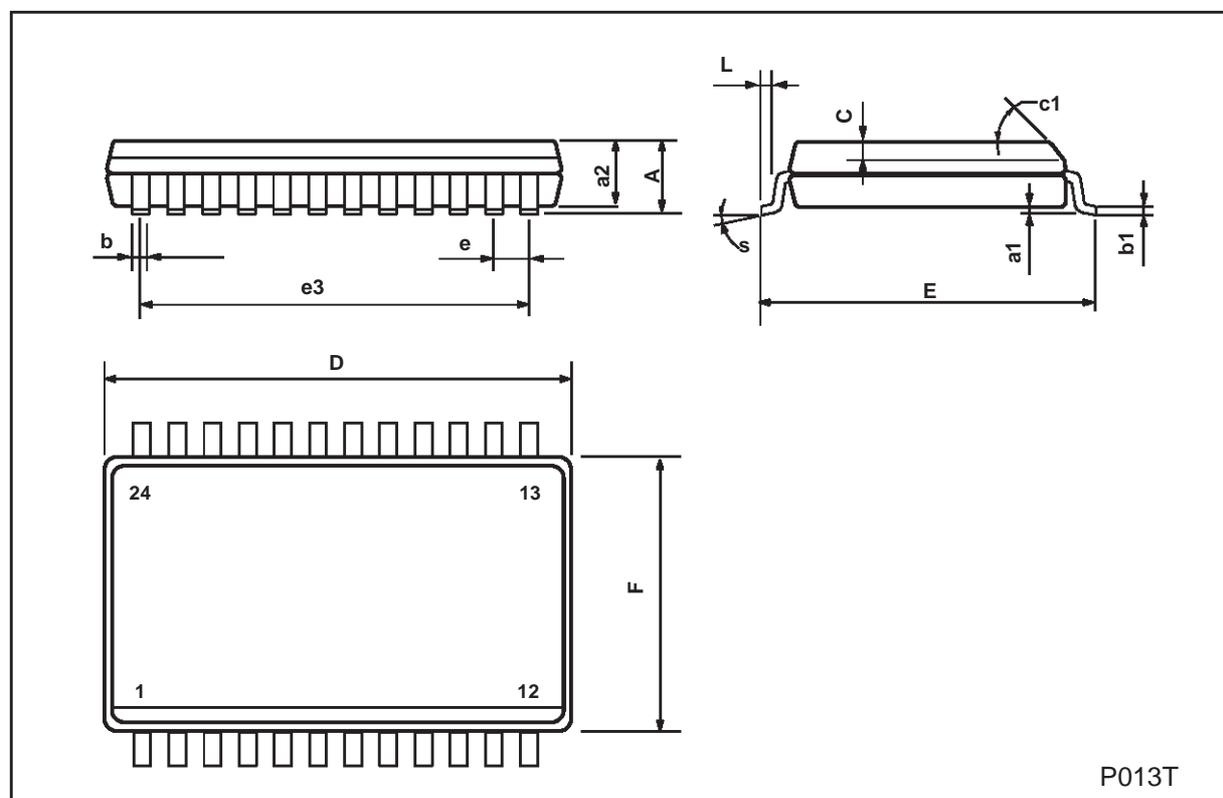


WAVEFORM 4: PULSE WIDTH



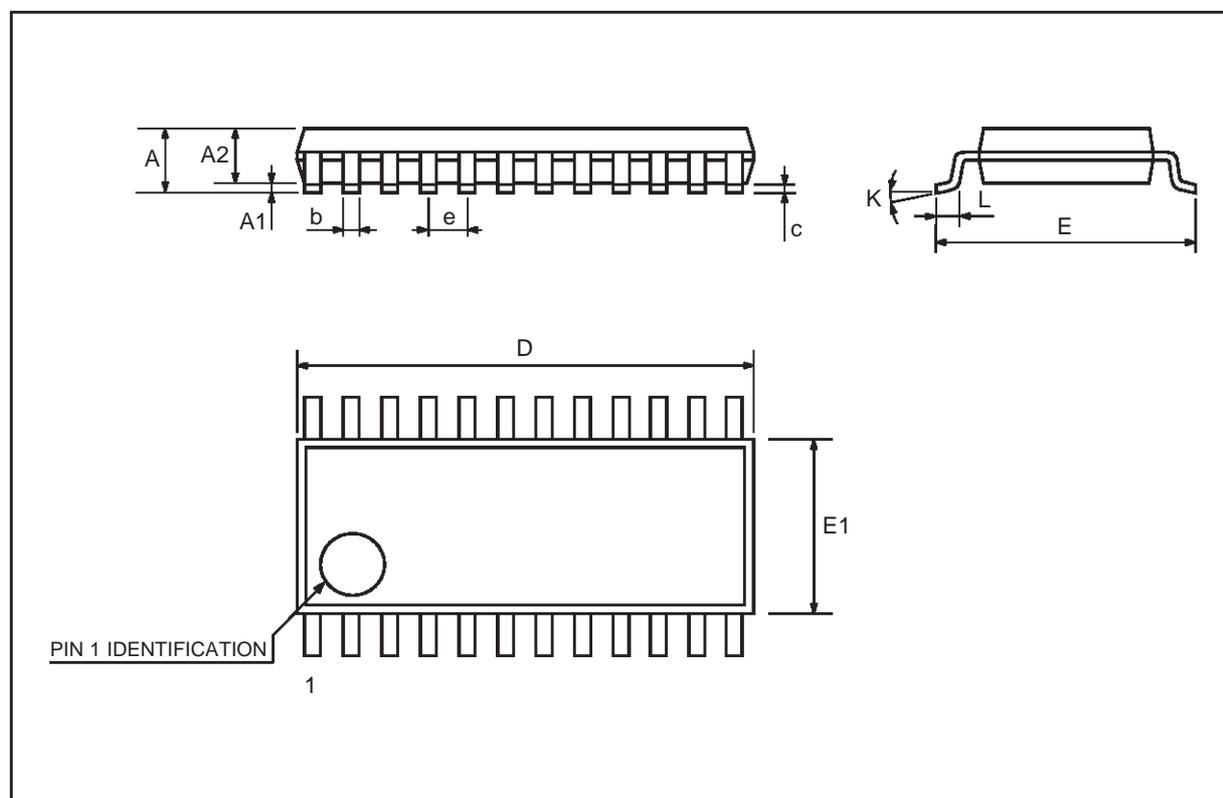
SO-24 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45 (typ.)					
D	15.20		15.60	0.598		0.614
E	10.00		10.65	0.393		0.420
e		1.27			0.05	
e3		13.97			0.55	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
S	8 (max.)					



TSSOP24 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.2	0.0035		0.0079
D	7.7	7.8	7.9	0.303	0.307	0.311
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°	4°	8°	0°	4°	8°
L	0.50	0.60	0.70	0.020	0.024	0.028



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